



ZXTD618MC

DUAL 20V NPN LOW SATURATION SWITCHING TRANSISTOR

Features and Benefits

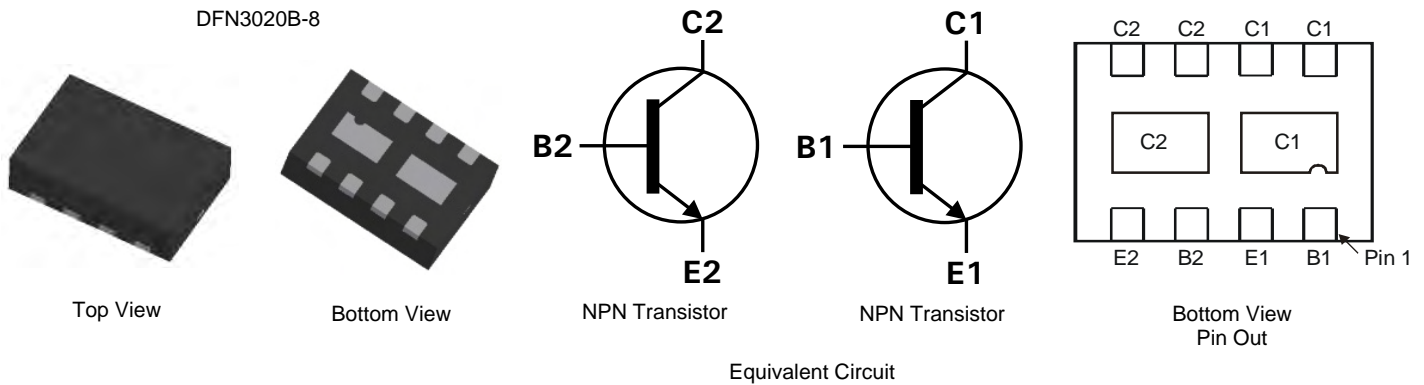
- $BV_{CEO} > 20V$
- $I_C = 4.5A$ Continuous Collector Current
- Low Saturation Voltage (150mV @ 1A)
- $R_{SAT} = 47m\Omega$ for a Low Equivalent On-Resistance
- h_{FE} specified up to 6A for high current gain hold up
- Dual NPN saving footprint and component count
- Low profile 0.8mm high package for thin applications
- $R_{\theta JA}$ efficient, 40% lower than SOT26
- 6mm² footprint, 50% smaller than TSOP6 and SOT26
- **Lead-Free, RoHS Compliant (Note 1)**
- **Halogen and Antimony Free. "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: DFN3020B-3
- Case material: Molded Plastic. "Green" Molding Compound.
- Terminals: Pre-Plated NiPdAu leadframe.
- UL Flammability Rating 94V-0
- Nominal package height: 0.8mm
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.013 grams (approximate)

Applications

- DC-DC Converters
- Charging circuits
- Motor control
- Power switches
- Portable applications



Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTD618MCTA	DBB	7	8	3,000

- Notes:
1. No purposefully added lead.
 2. Diodes Inc's "Green" Policy can be found on our website at <http://www.diodes.com>
 3. For Packaging Details, go to our website at <http://www.diodes.com>.

Marking Information



DBB = Product Type Marking Code
Top View, Dot Denotes Pin 1

Maximum Ratings @T_A = 25°C unless otherwise specified

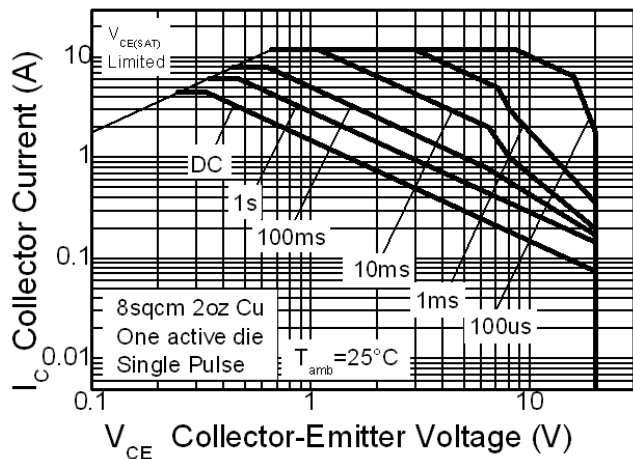
Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	20	
Emitter-Base Voltage	V _{EBO}	7	
Peak Pulse Current	I _{CM}	12	A
Continuous Collector Current (Notes 4 and 7)	I _C	4.5	
Continuous Collector Current (Notes 5 and 7)	I _C	5	
Base Current	I _B	1	

Thermal Characteristics @ T_A = 25°C unless otherwise specified

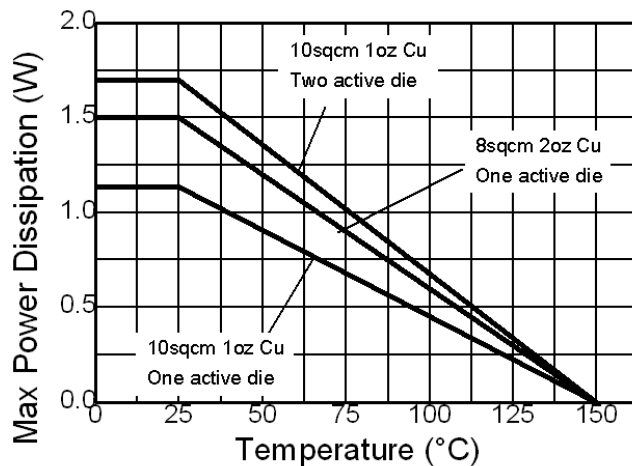
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P _D	1.5	W mW/°C
		12	
		2.45	
		19.6	
		1.13	
Thermal Resistance, Junction to Ambient	R _{θJA}	8	°C/W
		1.7	
		13.6	
		83.3	
		51.0	
Thermal Resistance, Junction to Lead	R _{θJL}	111	°C
(Notes 6 & 8)	73.5		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
4. For a dual device surface mounted on 28mm x 28mm (8cm²) FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The heatsink is split in half with the exposed collector pads connected to each half.
 5. Same as note (4), except the device is measured at t < 5 sec.
 6. Same as note (4), except the device is surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper.
 7. For a dual device with one active die.
 8. For dual device with 2 active die running at equal power.
 9. Thermal resistance from junction to solder-point (at the end of the collector lead).

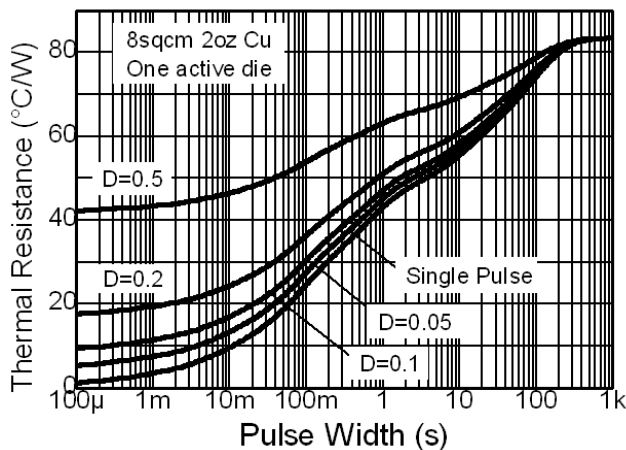
Thermal Characteristics



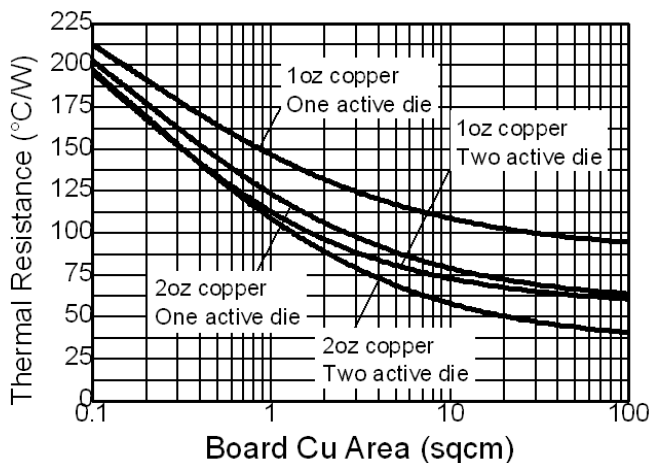
Safe Operating Area



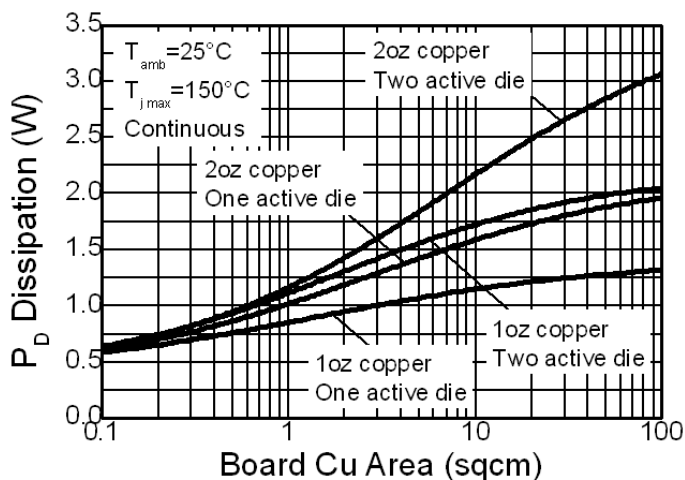
Derating Curve



Transient Thermal Impedance



Thermal Resistance v Board Area



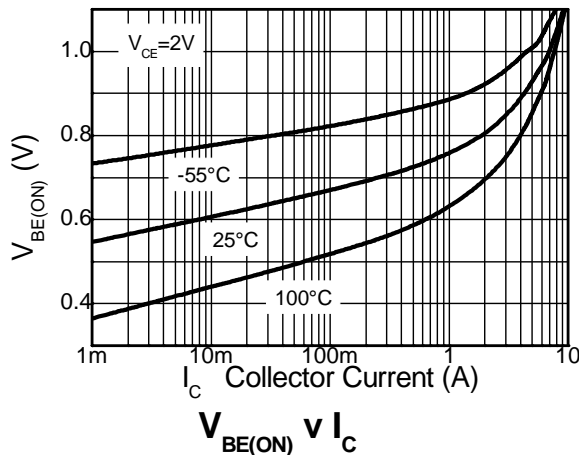
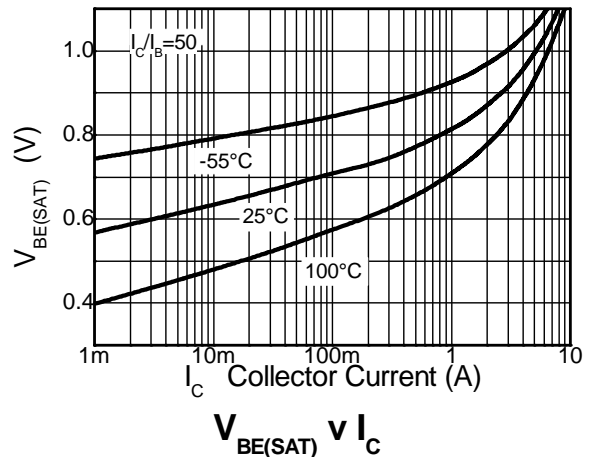
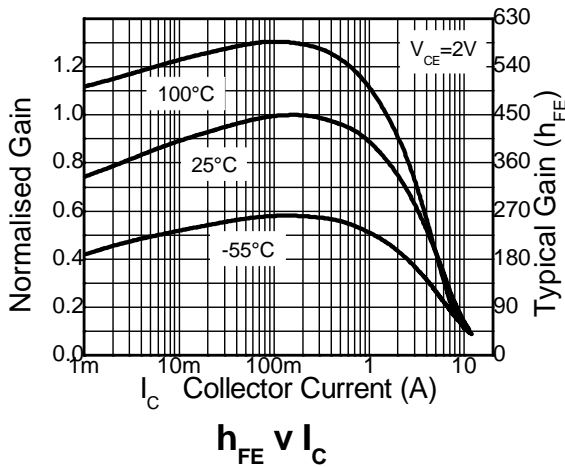
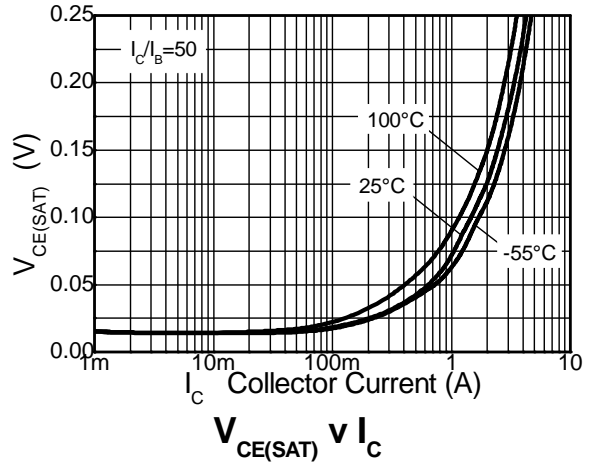
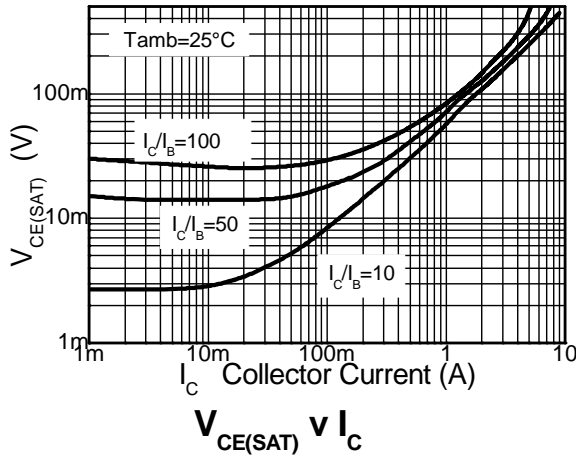
Power Dissipation v Board Area

Electrical Characteristics @T_A = 25°C unless otherwise specified

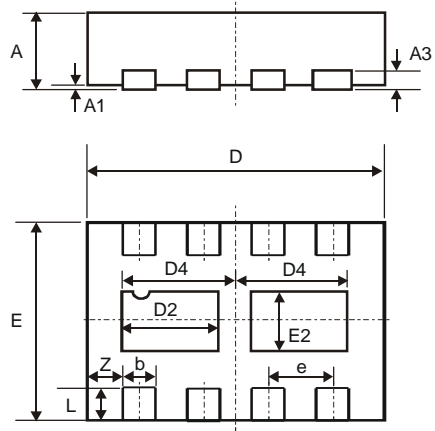
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	40	100	-	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	20	27	-	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7.0	8.2	-	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	-	-	100	nA	V _{CB} = 30V
Emitter Cutoff Current	I _{EBO}	-	-	100	nA	V _{EB} = 6V
Collector Emitter Cutoff Current	I _{CES}	-	-	100	nA	V _{CES} = 16V
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	200	400	-	-	I _C = 10mA, V _{CE} = 2V
		300	450	-		I _C = 200mA, V _{CE} = 2V
		200	360	-		I _C = 2A, V _{CE} = 2V
		100	180	-		I _C = 6A, V _{CE} = 2V
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	-	8	15	mV	I _C = 0.1A, I _B = 10mA
		-	90	150		I _C = 1A, I _B = 10mA
		-	115	135		I _C = 2A, I _B = 50mA
		-	190	250		I _C = 3A, I _B = 100mA
		-	210	300		I _C = 4.5A, I _B = 125mA
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	-	0.88	0.97	V	I _C = 4.5A, V _{CE} = 2V
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	-	0.98	1.07	V	I _C = 4.5A, I _B = 125mA
Output Capacitance	C _{obo}	-	23	30	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	f _T	100	140	-	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Turn-on Time	t _{on}	-	170	-	ns	V _{CC} = 10V, I _C = 3A
Turn-off Time	t _{off}	-	400	-	ns	I _{B1} = I _{B2} = 10mA

Notes: 10. Measured under pulsed conditions. Pulse width ≤ 300 μs. Duty cycle ≤ 2%

Typical Electrical Characteristics

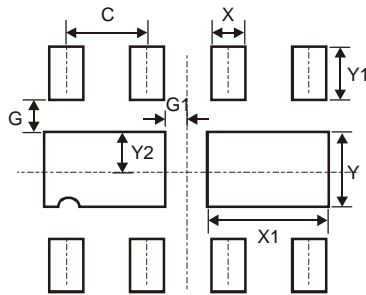


Package Outline Dimensions



DFN3020B-8			
Dim	Min	Max	Typ
A	0.77	0.83	0.80
A1	0	0.05	0.02
A3	-	-	0.15
b	0.25	0.35	0.30
D	2.95	3.075	3.00
D2	0.82	1.02	0.92
D4	1.01	1.21	1.11
e	-	-	0.65
E	1.95	2.075	2.00
E2	0.43	0.63	0.53
L	0.25	0.35	0.30
Z	-	-	0.375
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.650
G	0.285
G1	0.090
X	0.400
X1	1.120
Y	0.730
Y1	0.500
Y2	0.365

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